

SPECIFICATION AMENDMENTS

Replace the paragraph beginning at page 1, line 17 with:

~~With In~~ a field effect transistor in which a gallium nitride (GaN) ~~semiconductor~~ is used as the material of ~~a~~ the substrate, it is difficult to obtain excellent DC and high-frequency characteristics. This is due to ~~a trap which is present~~ traps at a surface of the substrate, and hence, it is necessary to stabilize the surface. According to a conventional technique, ~~a~~ the substrate is ~~irradiated~~ treated with a plasma of N₂, NH₃ or the like, so that voids created by nitrogen atoms, oxygen atoms and the like ~~existing~~ on ~~a~~ the surface of the gallium nitride substrate are ~~substituted with~~ replaced by nitrogen atoms (which is called nitriding), and the surface is stabilized (JP, 06-244409, A).

Replace the paragraph beginning at page 2, line 4 with:

However, ~~irradiation of plasma upon treatment of~~ a surface of a substrate ~~would~~ inevitably ~~result~~ results in plasma-induced damage, which ~~would~~ adversely ~~affect~~ affects electric characteristics and the like of a semiconductor device fabricated using such a substrate.